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INTEGRATED CIRCUITS, SILICON MONOLITHIC, BIPOLAR, ADVANCED LOW POWER SCHOTTKY,

QUAD, 2-LINE-TO-1-LINE DATA

SELECTOR/MULTIPLEXER WITH

3-STATE OUTPUTS,

BASED ON TYPE 54ALS257

ESCC Detail Specification No. 9408/032

ISSUE 1 October 2002



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Pages 1 to 30

INTEGRATED CIRCUITS, SILICON MONOLITHIC, BIPOLAR, ADVANCED LOW POWER SCHOTTKY, QUAD, 2-LINE-TO-1-LINE DATA SELECTOR/MULTIPLEXER WITH 3-STATE OUTPUTS, BASED ON TYPE 54ALS257 ESA/SCC Detail Specification No. 9408/032



space components coordination group

		Approved by					
lssue/Rev.	Date	SCCG Chairman	ESA Director General or his Deputy				
Issue 2	February 1992	Formers	to lake				
Revision 'A'	June 1994	Tomment	tim lut				



ISSUE 2

DOCUMENTATION CHANGE NOTICE

Rev. Letter	Rev. Date	CHANGE Reference Item	Approved DCR No.
		This Issue supersedes Issue 1 and incorporates all modifications defined in Revisions 'A' and 'B' to Issue 1 and the following DCR's:- Cover Page DCN Table 1(a) : Lead Material and/or Finish amended Figures 2 : Imperial dimensions and references deleted Figure 2(c) : In drawing, Note 6 corrected to "10" Notes to Figures : Title amended . : Note 1, amended to read "Figure 2(b)" Figure 3(a) : Comparison Table added Figure 3(b) : Note added Para. 4.2.2 : Deviation deleted, "None." added Para. 4.2.5 : Deviation deleted, "None." added Para. 4.5.2 : Amended to read "Figure 2(b)" Para. 4.5.3 : "Type Variant, as applicable" amended to refer to Table 1(a) Para. 4.5.3 : "Type Variant, as applicable" amended to refer to Table 1(a) Para. 4.6.3 : Reference to functional test sequence deleted Para. 4.6.3 : Reference to functional test sequence deleted Para. 4.6.3 : Figure corrected <td>None 22881 22881 23456 22881 22881 22881 22881 23456 21048 22919 22919 22919 2281 2281 23455 23455 23455 23455 23456 23456 23456</td>	None 22881 22881 23456 22881 22881 22881 22881 23456 21048 22919 22919 22919 2281 2281 23455 23455 23455 23455 23456 23456 23456
Ά'	June '94	P1. Cover Page P2. DCN P14. Para. 4.3.2 : Weights amended	None 221047

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APPENDICES (Applicable to specific Manufacturers only)

'A' Agreed Deviations for Texas Instruments (F)

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1. GENERAL

1.1 <u>SCOPE</u>

This specification details the ratings, physical and electrical characteristics, test and inspection data for a silicon monolithic, bipolar, advanced low power Schottky, Quad, 2-Line-to-1-Line Data Selector/Multiplexer with 3-State Outputs, based on Type 54ALS257. It shall be read in conjunction with ESA/SCC Generic Specification No. 9000, the requirements of which are supplemented herein.

1.2 COMPONENT TYPE VARIANTS

Variants of the basic type integrated circuits specified herein, which are also covered by this specification, are given in Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the integrated circuits specified herein, are as scheduled in Table 1(b).

1.4 PARAMETER DERATING INFORMATION (FIGURE 1)

Not applicable.

1.5 PHYSICAL DIMENSIONS

The physical dimensions of the integrated circuits specified herein are shown in Figure 2.

1.6 PIN ASSIGNMENT

As per Figure 3(a).

1.7 <u>TRUTH TABLE</u>

As per Figure 3(b).

- 1.8 <u>CIRCUIT SCHEMATIC</u> As per Figure 3(c).
- 1.9 FUNCTIONAL DIAGRAM

As per Figure 3(d).



- -

TABLE 1(a) - TYPE VARIANTS

VARIANT	CASE	FIGURE	LEAD MATERIAL AND/OR FINISH
01	FLAT	2(a)	D7
02	FLAT	2(a)	G4
03	CCP	2(b)	7
04	CCP	2(b)	4
05	DIL	2(c)	D7
06	DIL	2(c)	G4

TABLE 1(b) - MAXIMUM RATINGS

NO.	CHARACTERISTICS	SYMBOL	MAXIMUM RATINGS	UNIT	REMARKS
1	Supply Voltage	V _{CC}	-0.5 to 7.0	V	-
2	Input Voltage	V _{IN}	-0.5 to 7.0	V	Note 1
3	Voltage applied to a Disabled 3-State Output	VZ	5.5	V	-
4	Device Dissipation	PD	77	mWdc	Note 2
5	Operating Temperature Range	Т _{ор}	-55 to +125	°C	-
6	Storage Temperature Range	T _{stg}	-65 to +150	°C	-
7	Soldering Temperature For FP and DIP For CCP	T _{sol}	+ 265 + 245	°C	Note 3 Note 4

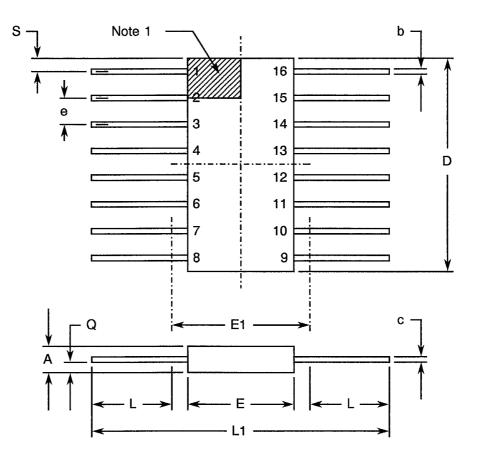
NOTES

- 1. Input Current limited to -18mA.
- 2. Must withstand added P_D due to short circuit conditions (i.e. I_{OS}) at 1 output for 5 seconds.
- 3. Duration 10 seconds maximum at a distance of not less than 1.5mm from the package and the same lead shall not be resoldered until 3 minutes have elapsed.
- 4. Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.



FIGURE 2 - PHYSICAL DIMENSIONS

FIGURE 2(a) - FLAT PACKAGE

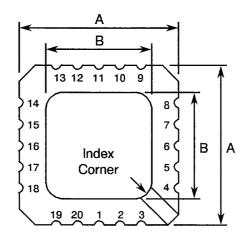


SYMBOL	MILLIM	NOTES	
STIVIBUL	MIN	MAX	NOTES
A	1.24	2.03	
b	0.38	0.48	8
с	0.08	0.15	8
D	9.65	11.02	
E	6.10	6.60	
E1	-	7.11	4
е	1.27 T	YPICAL	5, 9
L	6.35	9.40	
L1	19.05	-	
Q	0.25	0.89	2
S	0.25	0.76	7

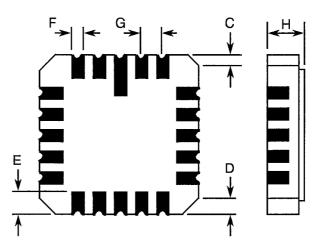


FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

FIGURE 2(b) - SQUARE CHIP CARRIER PACKAGE (3 LAYER BASE)



20 Terminal

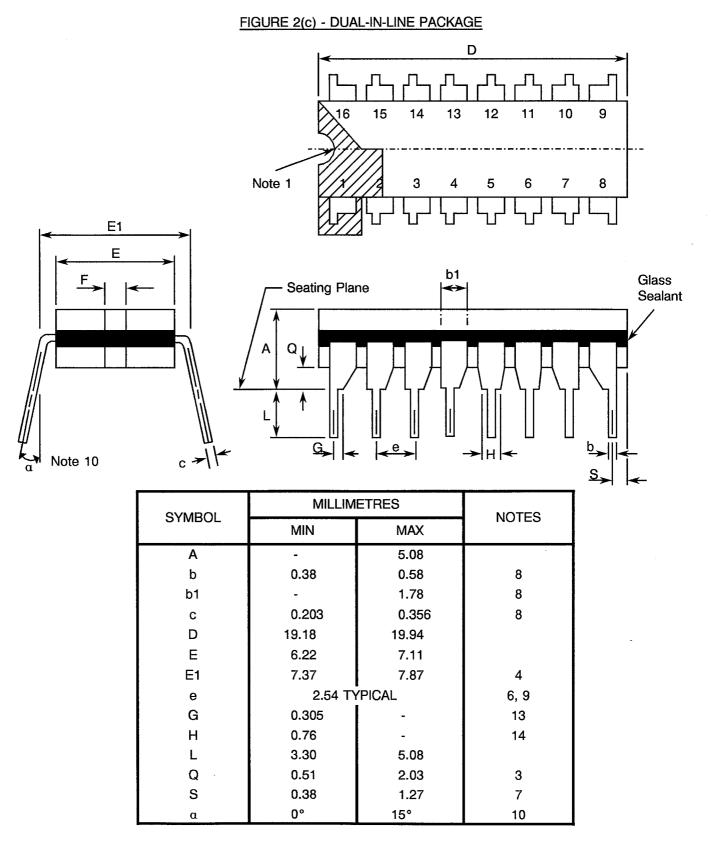


SYME	301	MILLIM	NOTES	
	502	MIN	MAX	NOTES
A		8.687	9.093	
В		7.798	9.093	
С		0.250	0.510	11
D		0.889	1.143	12
E		1.140	1.400	8
F	<u>.</u>	0.559	0.712	8
G	i	1.27 T	/PICAL	5, 9
н		1.630	2.540	



....

FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)



NOTES: See Page 10.



B....

FIGURE 2 - PHYSICAL DIMENSIONS (CONTINUED)

NOTES TO FIGURES 2(a) TO 2(c) INCLUSIVE

- 1. Index area; a notch or dot shall be located adjacent to Pin 1 and shall be within the shaded area shown. For chip carrier packages the index shall be as defined in Figure 2(b).
- 2. Dimension Q shall be measured at the point of exit of the lead from the body.
- 3. Dimension Q shall be measured from the seating plane to the base plane.
- 4. This dimension allows for off-centre lids, meniscus and glass overrun.
- 5. The true position pin or terminal spacing is 1.27mm between centrelines. Each pin or terminal centreline shall be located within ±0.13mm of its true longitudinal position relative to Pins 1 and the highest pin number.
- 6. The true position pin spacing is 2.54mm between centrelines. Each pin centreline shall be located within ±0.25mm of its true longitudinal position relative to Pins 1 and the highest pin number.
- 7. Applies to all 4 corners.
- 8. All leads or terminals.
- 9. 14 spaces for flat and dual-in-line packages.
 - 16 spaces for chip carrier packages.
- 10. Lead centre when α is 0°.
- 11. Index corner only 2 dimensions.
- 12. 3 non-index corners 6 dimensions.
- 13. 4 Terminals.
- 14. 12 Terminals.

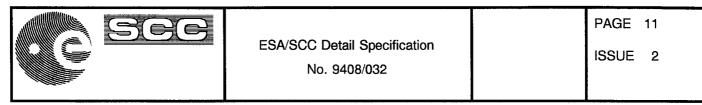
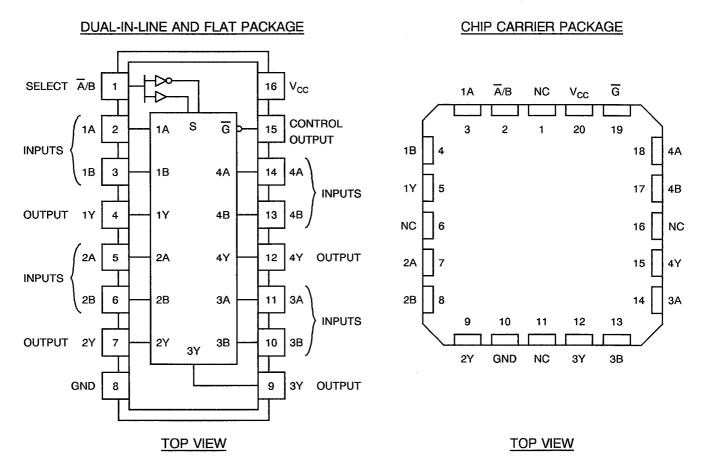


FIGURE 3(a) - PIN ASSIGNMENT



FLAT PACKAGE AND DUAL-IN-LINE TO CHIP CARRIER PIN ASSIGNMENT

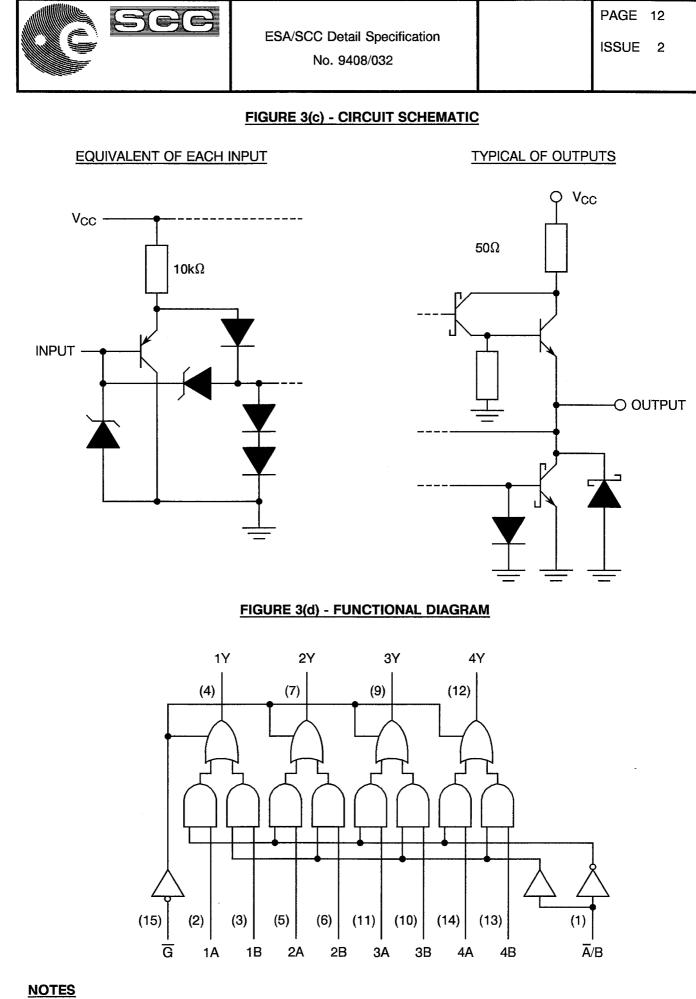
FLAT PACKAGE AND DUAL-IN-LINE PIN OUTS	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16
CHIP CARRIER PIN OUTS	2	3	4	5	7	8	9	10	12	13	14	15	17	18	19	20

FIGURE 3(b) - TRUTH TABLE

	OUTPUTS			
OUTPUT CONTROL	SELECT	DATA		V
G	Ā/B	А	В	
Н	Х	Х	Х	Z
L	L	L	х	L
Ŀ	L	н	x	н
L	Н	Х	L	L
L	Н	Х	Н	Н

NOTES

1. Logic Level Definitions: L=Low Level, H=High Level, Z=High Impedance, X=Irrelevant.



1. Pin numbers shown are for flat and dual-in-line packages; for chip carrier pins, see Figure 3(a).



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2. **APPLICABLE DOCUMENTS**

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 9000 for Integrated Circuits.
- (b) MIL-STD-883, Test Methods and Procedures for Micro-electronics.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply. In addition, the following abbreviation is used:-

- IOS/2 One half of the true output short circuit current.
- IOZH Off state, output current high.
- I_{OZL} Off state, output current low.
- I_{CCZ} Supply current outputs disabled.

4. REQUIREMENTS

4.1 GENERAL

The complete requirements for procurement of the integrated circuits specified herein shall be as stated in this specification and ESA/SCC Generic Specification No. 9000 for Integrated Circuits. Deviations from the Generic Specification, applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 DEVIATIONS FROM GENERIC SPECIFICATION

- 4.2.1 **Deviations from Special In-process Controls** None.
- 4.2.2 Deviations from Final Production Tests (Chart II) None.
- 4.2.3 Deviations from Burn-in Tests (Chart III)
 - "High Temperature Reverse Bias" (a) Para. 7.1.1(a), tests and subsequent electrical measurements related to this test shall be omitted.
 - (b) Para. 9.9.2, "Electrical Measurements at High and Low Temperatures": Only a test result summary, based on go-no-go tests and presented in histogram form is required.

4.2.4 Deviations from Qualification Tests (Chart IV) None.



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Rev. 'A'

4.2.5 Deviations from Lot Acceptance Tests (Chart V)

None.

4.3 MECHANICAL REQUIREMENTS

4.3.1 Dimension Check

The dimensions of the integrated circuits specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the integrated circuits specified herein shall be 0.7 grammes for the flat package, 0.6 grammes for the chip carrier package and 2.2 grammes for the dual-in-line package.

4.4 MATERIALS AND FINISHES

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the integrated circuits specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

4.4.1 <u>Case</u>

The case shall be hermetically sealed and have a metal body with hard glass seals or a ceramic body and the lids shall be welded, brazed, preform-soldered or glass frit-sealed.

4.4.2 Lead Material and Finish

For dual-in-line and flat packages, the material shall be either Type 'D' or Type 'G' with either Type '4' or Type '7' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500. For chip carrier packages, the finish shall be either Type '4' or Type '7' in accordance with the requirements of ESA/SCC Basic Specification No. 23500. (See Table 1(a) for Type Variants).

4.5 MARKING

4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

4.5.2 Lead Identification

For dual-in-line and flat packages, an index shall be located at the top of the package in the position defined in Note 1 to Figure 2 or, alternatively, a tab may be used to identify Pin No. 1. The pin numbering must be read with the index or tab on the left-hand side. For chip carrier packages, the index shall be as defined by Figure 2(b).



4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:

	<u>940803202</u> Ę
Detail Specification Number	
Type Variant (see Table 1(a))	
Testing Level (B or C, as applicable)	

4.5.4 Traceability Information

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

4.6 ELECTRICAL MEASUREMENTS

4.6.1 Electrical Measurements at Room Temperature

The parameters to be measured in respect of electrical characteristics are scheduled in Table 2. Unless otherwise specified, the measurements shall be performed at T_{amb} = +22±3 °C.

4.6.2 Electrical Measurements at High and Low Temperatures

The parameters to be measured at high and low temperatures are scheduled in Table 3. The measurements shall be performed at $T_{amb} = +125(+0-5)$ °C and -55(+5-0) °C respectively.

4.6.3 Circuits for Electrical Measurements

Circuits for use in performing electrical measurements listed in Tables 2 and 3 of this specification are shown in Figure 4.

4.7 BURN-IN TESTS

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, measurements shall be performed at $T_{amb} = +22 \pm 3$ °C. The parameter drift values (Δ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

4.7.2 Conditions for Power Burn-in

The requirements for power burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 9000. The conditions for power burn-in shall be as specified in Table 5 of this specification.

4.7.3 Electrical Circuits for Power Burn-in

Circuits for use in performing the power burn-in tests are shown in Figure 5 of this specification.



TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIM	IITS	UNIT
NO.		STWDOL	MIL-STD 883	FIG.	D/F = DIP AND FP C = CCP)	MIN	MAX	
1	Functional Test	-	-	3(b)	Verify Truth Table with Load. Note 1	-	-	-
2 to 11	Input Current High Level 1	liH1	3010	4(a)	V _{CC} = 5.5V, V _{IN} = 2.7V (Pins D/F 1-2-3-5-6-10-11- 13-14-15) (Pins C 2-3-4-7-8-13-14- 17-18-19)	-	20	μΑ
12 to 21	Input Current High Level 2 (Max. Input Voltage)	I _{IH2}	3010	4(a)	V _{CC} = 5.5V, V _{IN} = 7.0V (Pins D/F 1-2-3-5-6-10-11- 13-14-15) (Pins C 2-3-4-7-8-13-14- 17-18-19)	-	100	μΑ
22 to 31	Input Clamp Voltage	V _{IC}	3008	4(b)	V _{CC} = 4.5V, I _{IN} = 18mA Note 2 (Pins D/F 1-2-3-5-6-10-11- 13-14-15) (Pins C 2-3-4-7-8-13-14- 17-18-19)	•	- 1.5	V
32 to 41	Input Current Low Level	ΙL	3009	4(c)	V _{CC} = 5.5V, V _{IL} = 0.4V (Pins D/F 1-2-3-5-6-10-11- 13-14-15) (Pins C 2-3-4-7-8-13-14- 17-18-19)	-	- 100	μА
42 to 45	Output Voltage Low Level	V _{OL}	3007	4(d)	$V_{CC} = 4.5V, V_{IH} = 2.0V$ $V_{IL} = 0.7V, I_{OL} = 12mA$ (Pins D/F 4-7-9-12) (Pins C 5-9-12-15)	-	0.4	V
46 to 49	Output Voltage High Level 1	V _{OH1}	3006	4(e)	$V_{CC} = 4.5V, V_{IH} = 2.0V$ $V_{IL} = 0.7V, I_{OH} = -1.0mA$ (Pins D/F 4-7-9-12) (Pins C 5-9-12-15)	2.4	-	V
50 to 53	Output Voltage High Level 2	V _{OH2}	3006	4(e)	$V_{CC} = 4.5V, V_{IH} = 2.0V$ $V_{IL} = 0.7V, I_{OH} = -400\mu A$ (Pins D/F 4-7-9-12) (Pins C 5-9-12-15)	2.5	-	V
54 to 57	Output Voltage High Level 3	V _{OH3}	3006	4(e)	V _{CC} = 5.5V, V _{IH} = 2.0V V _{IL} = 0.7V, I _{OH} = -400µA (Pins D/F 4-7-9-12) (Pins C 5-9-12-15)	3.5	-	V



TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS (CONT'D)

NO.	CHARACTERISTICS	CHARACTERISTICS SYMBOL		TEST	TEST CONDITIONS (PINS UNDER TEST	LIMITS		UNIT
NO.		OTMIDOL	MIL-STD FIG. D/F = DIP AND FP 883 C = CCP)		D/F = DIP AND FP C = CCP)	MIN	MAX	UNIT
58 to 61	One Half of the True Output Short Circuit Current	I _{OS/2}	3011	4(f)	V _{CC} = 5.5V, V _{OUT} = 2.25V Note 3 (Pins D/F 4-7-9-12) (Pins C 5-9-12-15)	-30	112	mA
62 to 65	Off State Output Current High Level Applied	l _{OZH}	-	4(g)	V _{CC} = 5.5V, V _{OUT} = 2.7V (Pins D/F 4-7-9-12) (Pins C 5-9-12-15)	-	20	μA
66 to 69	Off State Output Current Low Level Applied	I _{OZL}	-	4(g)	V _{CC} = 5.5V, V _{OUT} = 0.4V (Pins D/F 4-7-9-12) (Pins C 5-9-12-15)	-	-20	μА
70	Supply Current Outputs High	Iссн	3005	4(h)	V _{CC} = 5.5V Note 4 (Pin D/F 16) (Pin C 20)	-	6.0	mA
71	Supply Current Outputs Low	ICCL	3005	4(h)	V _{CC} = 5.5V Note 4 (Pin D/F 16) (Pin C 20)	-	12	mA
72	Supply Current Outputs Disabled	lccz	3005	4(h)	V _{CC} = 5.5V Note 4 (Pin D/F 16) (Pin C 20)	-	14	mA



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TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP	LIM	ITS	UNIT
NO.	CHANACTERISTICS	STNBOL	MIL-STD 883			MIN	MAX	UNIT
73 to 88	Propagation Delay Low to High, from A or B to any Y	t₽LH	3003	4(i)	$\begin{array}{c} V_{CC} = 4.5 \text{ and } 5.5V \\ C_L = 50 pF, \ R_1 = R_2 = 500 \Omega \\ \hline Pins \ D/F & Pins \ C \\ \hline 2 \ to & 4 & 3 \ to & 5 \\ \hline 3 \ to & 4 & 4 \ to & 5 \\ \hline 5 \ to & 7 & 7 \ to & 9 \\ \hline 6 \ to & 7 & 8 \ to & 9 \\ \hline 10 \ to & 9 & 13 \ to & 12 \\ \hline 11 \ to & 9 & 14 \ to & 12 \\ \hline 13 \ to & 12 & 17 \ to & 15 \\ \hline 14 \ to & 12 & 18 \ to & 15 \\ \end{array}$	2.0	12	ns
89 to 104	Propagation Delay High to Low, from A or B to any Y	t₽HL	3003	4(i)	$\begin{array}{c} V_{CC} = 4.5 \text{ and } 5.5V \\ C_L = 50 pF, \ R_1 = R_2 = 500 \Omega \\ \hline Pins \ D/F \\ 2 \ to \ 4 \\ 3 \ to \ 5 \\ 3 \ to \ 4 \\ 4 \ to \ 5 \\ 5 \ to \ 7 \\ 7 \ to \ 9 \\ 6 \ to \ 7 \\ 8 \ to \ 9 \\ 10 \ to \ 9 \\ 13 \ to \ 12 \\ 11 \ to \ 9 \\ 14 \ to \ 12 \\ 13 \ to \ 12 \\ 18 \ to \ 15 \\ 14 \ to \ 12 \\ \end{array}$	3.0	14	ns
105 to 112	Propagation Delay Low to High from Ā/B to any Y	t _{PLH}	3003	4(i)	$\begin{array}{c} V_{CC} = 4.5 \text{ and } 5.5 V \\ C_L = 50 pF, \ R_1 = R_2 = 500 \Omega \\ \hline Pins \ D/F & Pins \ C \\ \hline 1 \ to \ 4 & 2 \ to \ 5 \\ 1 \ to \ 7 & 2 \ to \ 9 \\ 1 \ to \ 9 & 2 \ to \ 12 \\ 1 \ to \ 12 & 2 \ to \ 15 \end{array}$	7.0	21	ns
113 to 120	Propagation Delay High to Low from Ā/B to any Y	tρhl	3003	4(i)	$\begin{array}{c} V_{CC} = 4.5 \text{ and } 5.5 V \\ C_L = 50 pF, \ R_1 = R_2 = 500 \Omega \\ \underline{Pins \ D/F} & \underline{Pins \ C} \\ 1 \ to & 4 & 2 \ to & 5 \\ 1 \ to & 7 & 2 \ to & 9 \\ 1 \ to & 9 & 2 \ to & 12 \\ 1 \ to & 12 & 2 \ to & 15 \\ \end{array}$	6.0	25	ns



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TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS (CONT'D)

NO	NO. CHARACTERISTICS SY		TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST D/F = DIP AND FP	LIMITS		UNIT
NO.	CHARACTERISTICS	SYMBOL	MIL-STD FIG. 5/ 883		C = CCP) (NOTE 5)	MIN	MAX	UNIT
121 to 128	Output Enable Time to High Level from G to any Y	tрzн	3003	4(i)	$\begin{array}{c} V_{CC} = 4.5 \text{ and } 5.5V \\ C_L = 50 pF, \ R_1 = R_2 = 500\Omega \\ \hline Pins \ D/F & Pins \ C \\ 15 \ to & 4 & 19 \ to & 5 \\ 15 \ to & 7 & 19 \ to & 9 \\ 15 \ to & 9 & 19 \ to & 12 \\ 15 \ to & 12 & 19 \ to & 15 \end{array}$	4.0	20	ns
129 to 136	Output Enable Time to Low Level from G to any Y	ťΡΖL	3003	4(i)	$\begin{array}{rrr} V_{CC} = 4.5 \mbox{ and } 5.5V \\ C_L = 50pF, \ R_1 = R_2 = 500\Omega \\ \hline Pins \ D/F & Pins \ C \\ 15 \ to & 4 & 19 \ to & 5 \\ 15 \ to & 7 & 19 \ to & 9 \\ 15 \ to & 9 & 19 \ to & 12 \\ 15 \ to & 12 & 19 \ to & 15 \\ \end{array}$	5.0	22	ns
137 to 144	Output Disable Time to High Level from G to any Y	ţрнz	3003	4(i)	$\begin{array}{c} V_{CC} = 4.5 \text{ and } 5.5V\\ C_L = 50 pF, \ R_1 = R_2 = 500 \Omega\\ \hline Pins \ D/F & Pins \ C\\ 15 \ to & 4 & 19 \ to & 5\\ 15 \ to & 7 & 19 \ to & 9\\ 15 \ to & 9 & 19 \ to & 12\\ 15 \ to & 12 & 19 \ to & 15 \end{array}$	2.0	12	ns
145 to 152	Output Disable Time to Low Level from G to any Y	t _{PLZ}	3003	4(i)	$\begin{array}{c} V_{CC} = 4.5 \text{ and } 5.5V \\ C_L = 50 pF, \ R_1 = R_2 = 500 \Omega \\ \underline{Pins \ D/F} & \underline{Pins \ C} \\ 15 \ to & 4 & 19 \ to & 5 \\ 15 \ to & 7 & 19 \ to & 9 \\ 15 \ to & 9 & 19 \ to & 12 \\ 15 \ to & 12 & 19 \ to & 15 \end{array}$	4.0	18	ns

NOTES

- 1. Go-no-go test with V_{IL} = 0.3V, V_{IH} = 3.0V, trip point 1.5V.
- 2. All inputs and outputs not under test shall be open.
- 3. No more than 1 output should be tested at a time.
- 4. For I_{CCH}: G Grounded, A/B at 4.5V, B inputs at 4.5V, A inputs Grounded.

For I_{CCL}: G Grounded, A/B Grounded, all inputs as for I_{CCH}.

- For I_{CCZ}: G at 4.5V.
- 5. Propagation delay measurements shall be performed as a go-no-go test on a 100% basis. Read-and-record measurements shall be performed on an LTPD7 sample basis following the Chart III Burn-in Test.



TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES, + 125(+0-5) °C AND -55(+5-0) °C

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIMITS		UNIT
NO.	CHANACTERISTICS	STNDUL	MIL-STD 883	FIG.	D/F = DIP AND FP C = CCP)	MIN	MAX	UNIT
1	Functional Test	-	-	3(b)	Verify Truth Table with Load. Note 1	-	-	-
2 to 11	Input Current High Level 1	liH1	3010	4(a)	V _{CC} = 5.5V, V _{IN} = 2.7V (Pins D/F 1-2-3-5-6-10-11- 13-14-15) (Pins C 2-3-4-7-8-13-14- 17-18-19)	1	20	μΑ
12 to 21	Input Current High Level 2 (Max. Input Voltage)	I _{IH2}	3010	4(a)	V _{CC} = 5.5V, V _{IN} = 7.0V (Pins D/F 1-2-3-5-6-10-11- 13-14-15) (Pins C 2-3-4-7-8-13-14- 17-18-19)	-	100	μΑ
22 to 31	Input Clamp Voltage	V _{IC}	3008	4(b)	V _{CC} = 4.5V, I _{IN} = 18mA Note 2 (Pins D/F 1-2-3-5-6-10-11- 13-14-15) (Pins C 2-3-4-7-8-13-14- 17-18-19)	-	- 1.5	V
32 to 41	Input Current Low Level	Ι _{ΙL}	3009	4(c)	V _{CC} = 5.5V, V _{IL} = 0.4V (Pins D/F 1-2-3-5-6-10-11- 13-14-15) (Pins C 2-3-4-7-8-13-14- 17-18-19)	-	- 100	μА
42 to 45	Output Voltage Low Level	V _{OL}	3007	4(d)	$V_{CC} = 4.5V, V_{IH} = 2.0V$ $V_{IL} = 0.7V, I_{OL} = 12mA$ (Pins D/F 4-7-9-12) (Pins C 5-9-12-15)	-	0.4	V
46 to 49	Output Voltage High Level 1	V _{OH1}	3006	4(e)	$V_{CC} = 4.5V, V_{IH} = 2.0V$ $V_{IL} = 0.7V, I_{OH} = -1.0mA$ (Pins D/F 4-7-9-12) (Pins C 5-9-12-15)	2.4	-	V
50 to 53	Output Voltage High Level 2	V _{OH2}	3006	4(e)	$V_{CC} = 4.5V, V_{IH} = 2.0V$ $V_{IL} = 0.7V, I_{OH} = -400\mu A$ (Pins D/F 4-7-9-12) (Pins C 5-9-12-15)	2.5	-	V
54 to 57	Output Voltage High Level 3	V _{OH3}	3006	4(e)	$V_{CC} = 5.5V, V_{IH} = 2.0V$ $V_{IL} = 0.7V, I_{OH} = -400\mu A$ (Pins D/F 4-7-9-12) (Pins C 5-9-12-15)	3.5	-	V

NOTES: See Page 19.



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TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES, + 125(+0-5) °C AND -55(+5-0) °C (CONT'D)

NO.	CHARACTERISTICS	SYMBOL	TEST METHOD	TEST	TEST CONDITIONS (PINS UNDER TEST	LIMITS		UNIT
140.		OTMBOL	MIL-STD FIG. D/F = DIP AND FP 883 C = CCP)		MIN	MAX	UNIT	
58 to 61	One Half of the True Output Short Circuit Current	I _{OS/2}	3011	4(f)	V _{CC} = 5.5V, V _{OUT} = 2.25V Note 3 (Pins D/F 4-7-9-12) (Pins C 5-9-12-15)	-30	- 112	mA
62 to 65	Off State Output Current High Level Applied	l _{оzн}	-	4(g)	V _{CC} = 5.5V, V _{OUT} = 2.7V (Pins D/F 4-7-9-12) (Pins C 5-9-12-15)	-	20	μА
66 to 69	Off State Output Current Low Level Applied	lozl	-	4(g)	V _{CC} = 5.5V, V _{OUT} = 0.4V (Pins D/F 4-7-9-12) (Pins C 5-9-12-15)	-	-20	μA
70	Supply Current Outputs High	Іссн	3005	4(h)	V _{CC} = 5.5V Note 4 (Pin D/F 16) (Pin C 20)	-	6.0	mA
71	Supply Current Outputs Low	lcc∟	3005	4(h)	V _{CC} = 5.5V Note 4 (Pin D/F 16) (Pin C 20)	-	12	mA
72	Supply Current Outputs Disabled	lccz	3005	4(h)	V _{CC} = 5.5V Note 4 (Pin D/F 16) (Pin C 20)	-	14	mA

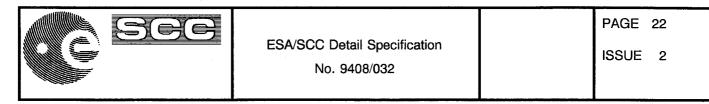
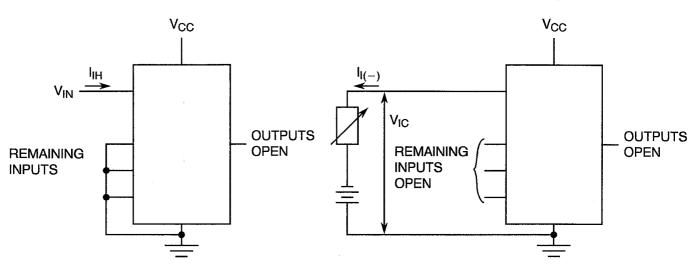


FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

FIGURE 4(a) - INPUT CURRENT HIGH LEVEL

FIGURE 4(b) - INPUT CLAMP VOLTAGE



NOTES

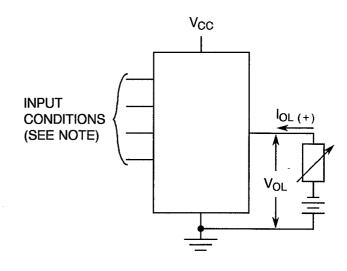
1. Each input to be tested separately.

- NOTES
- 1. Each input to be tested separately.

FIGURE 4(c) - LOW LEVEL INPUT CURRENT

5.5V V_{CC} REMAINING INPUTS V_I U V_I OUTPUTS OPEN

FIGURE 4(d) - LOW LEVEL OUTPUT VOLTAGE



NOTES

1. Each input to be tested separately.



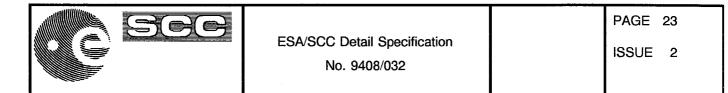


FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

NOTES

1. Test per Truth Table.

FIGURE 4(g) - OFF STATE OUTPUT CURRENT

FIGURE 4(e) - HIGH LEVEL OUTPUT VOLTAGE

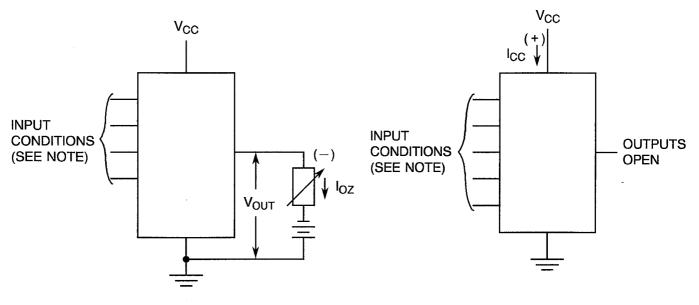
NOTES

- 1. G and A/B grounded, Data A input at VIH min.
- 2. No more than 1 output should be tested at a time.

FIGURE 4(f) - ONE HALF SHORT CIRCUIT

FIGURE 4(h) - SUPPLY CURRENT

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NOTES

1. \overline{G} = 5.5V for high Z output (See Figure 3(b)).

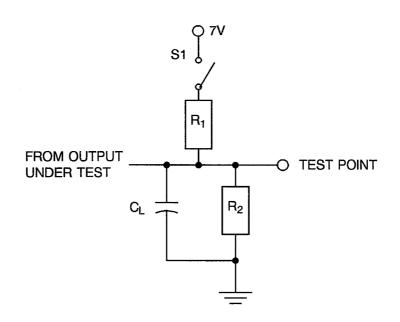
NOTES

1. See Note 4 on Page 19.

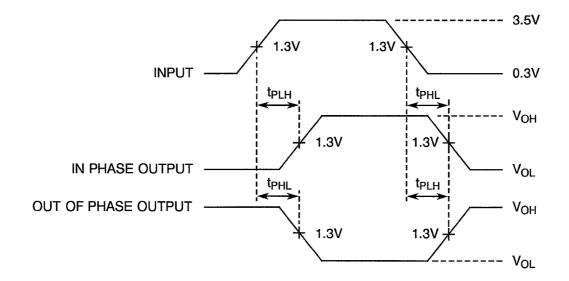


FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(i) - DYNAMIC TEST AND SWITCHING WAVEFORMS



VOLTAGE WAVEFORMS - PROPAGATION DELAY TIMES



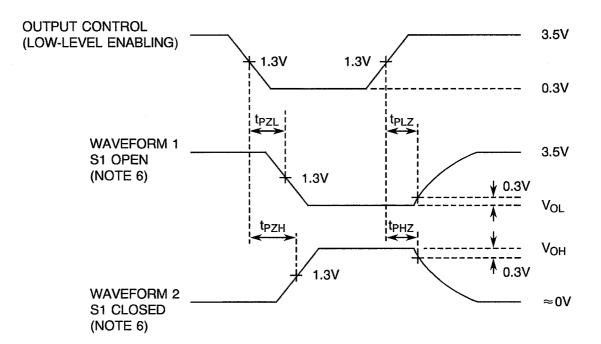
NOTES: See Note 5 on Page 25.



FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS (CONTINUED)

FIGURE 4(i) - DYNAMIC TEST AND SWITCHING WAVEFORMS (CONTINUED)

VOLTAGE WAVEFORMS - ENABLE AND DISABLE TIMES



NOTES

- 1. The generator has the following characteristics: $t_r = t_f = 2ns$, PRR = 1MHz, $Z_{out} = 50\Omega$, Duty Cycle = 50%.
- 2. $C_L = 50 pF \pm 5\%$ including scope probe, wiring and stray capacitance without package in test fixture.
- 3. Each output tested separately.
- 4. $R_1 = R_2 = 500\Omega \pm 5\%$.
- 5. For measurement of propagation time switch S1 is open.
- 6. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.

Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.



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TABLE 4 - PARAMETER DRIFT VALUES

NO.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITIONS	CHANGE LIMITS (Δ)	UNIT
2 to 11	Input Current High Level 1	liH1	As per Table 2	As per Table 2	±20 or (1) ±0.5	% µА
32 to 41	Input Current Low Level	l _{IL}	As per Table 2	As per Table 2	±10	μA
42 to 45	Output Voltage Low Level	V _{OL}	As per Table 2	As per Table 2	±60	mV
46 to 49	Output Voltage High Level 1	V _{OH1}	As per Table 2	As per Table 2	±200	mV
50 to 53	Output Voltage High Level 2	V _{OH2}	As per Table 2	As per Table 2	± 200	mV
54 to 57	Output Voltage High Level 3	V _{OH3}	As per Table 2	As per Table 2	±200	mV

NOTES

1. Whichever is greater referred to the initial value.

TABLE 5 - CONDITIONS FOR POWER BURN-IN AND OPERATING LIFE TEST

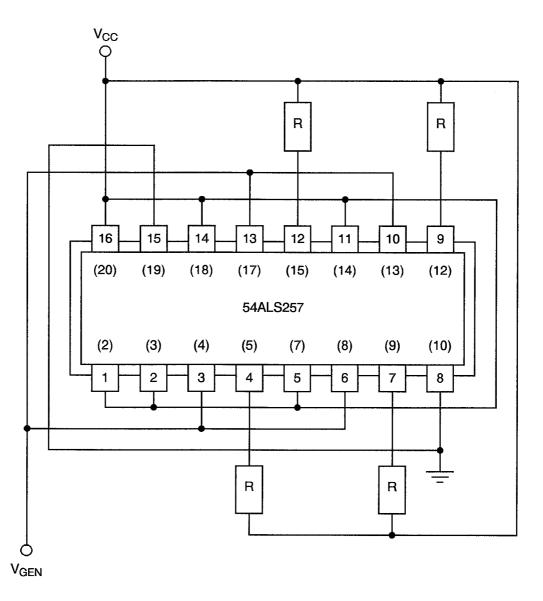
NO.	CHARACTERISTICS	SYMBOL	CONDITION	UNIT
1	Ambient Temperature	T _{amb}	+ 125(+ 0 - 5)	°C
2	Power Supply Voltage	V _{CC}	+5(+0.5-0)	V
3	Pulse Voltage	V _{GEN}	0.5 max. to 3.0 min.	Vac
4	Frequency	f	100 (See Note 1)	Hz
5	Fan-out	-	10	-
6	Rise Time	t _r	50 max.	μs
7	Fall Time	t _f	50 max.	μs
8	Duty Cycle	-	20 min.	%

NOTES

1. Tolerance ±10%.



FIGURE 5 - ELECTRICAL CIRCUIT FOR POWER BURN-IN AND OPERATING LIFE TEST



NOTES

- 1. Pin numbers in parenthesis are for the chip carrier package.
- 2. $R = 380\Omega$.



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4.8 <u>ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC</u> SPECIFICATION NO. 9000)

4.8.1 Electrical Measurements on Completion of Environmental Tests

The parameters to be measured on completion of environmental tests are scheduled in Table 6. Unless otherwise stated, the measurements shall be performed at T_{amb} = +22±3 °C.

4.8.2 Electrical Measurements at Intermediate Points during Endurance Tests

The parameters to be measured at intermediate points during endurance tests are as scheduled in Table 6 of this specification. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C.

4.8.3 Electrical Measurements on Completion of Endurance Tests

The parameters to be measured on completion of endurance testing are as scheduled in Table 6 of this specification. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3 \text{ °C}$.

4.8.4 <u>Conditions for Operating Life Tests</u>

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 9000. The conditions for operating life testing shall be as specified in Table 5 of this specification.

4.8.5 <u>Electrical Circuits for Operating Life Tests</u>

Circuits for use in performing the operating life tests are shown in Figure 5.

4.8.6 Conditions for High Temperature Storage Test

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 9000. The conditions for high temperature storage shall be $T_{amb} = +150(+0.5)$ °C.



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TABLE 6 - ELECTRICAL MEASUREMENTS ON COMPLETION OF ENVIRONMENTAL TESTS AND AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTS

NO.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR	TEST	CHAN	ge limits	UNIT
NO.	CHARACTERISTICS	TEST METHOD		CONDITIONS	(Δ)	ABSOLUTE	UNIT
2 to 11	Input Current High Level 1	l _{IH1}	As per Table 2	As per Table 2	±1	-	μA
12 to 21	Input Current High Level 2 (Max. Input Voltage)	I _{IH2}	As per Table 2	As per Table 2	-	100	μΑ
32 to 41	Input Current Low Level	Ι _{ΙL}	As per Table 2	As per Table 2	±10	-	μΑ
42 to 45	Output Voltage Low Level	V _{OL}	As per Table 2	As per Table 2	±60	-	mV
46 to 49	Output Voltage High Level 1	V _{OH1}	As per Table 2	As per Table 2	±200	-	mV
50 to 53	Output Voltage High Level 2	V _{OH2}	As per Table 2	As per Table 2	±200	-	mV
54 to 57	Output Voltage High Level 3	V _{OH3}	As per Table 2	As per Table 2	±200	-	mV
70	Supply Current Outputs High	Іссн	As per Table 2	As per Table 2	±20	-	%
71	Supply Current Outputs Low	ICCL	As per Table 2	As per Table 2	±20	-	%
72	Supply Current Outputs Disabled	lccz	As per Table 2	As per Table 2	±20	-	%



ESA/SCC Detail Specification

No. 9408/032

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APPENDIX 'A'

Page 1 of 1

AGREED DEVIATIONS FOR TEXAS INSTRUMENTS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS			
Para. 4.2.1	canning Electron Microscope (SEM) Inspection may be performed using IF document TIF 3.61.610.001.			
Para. 4.2.2	rior to Die Shear Test TIF may perform a Radiographic Inspection on the andomly chosen samples to be subjected to this test, using TIF document I 50.42-3002.			
Para. 4.2.3	Radiographic Inspection may be performed using TIF document TI 50.42-3002.			